

Supporting Information

Gd-doped diamond synthesized by Gd@C₈₂ under high pressure and high temperature

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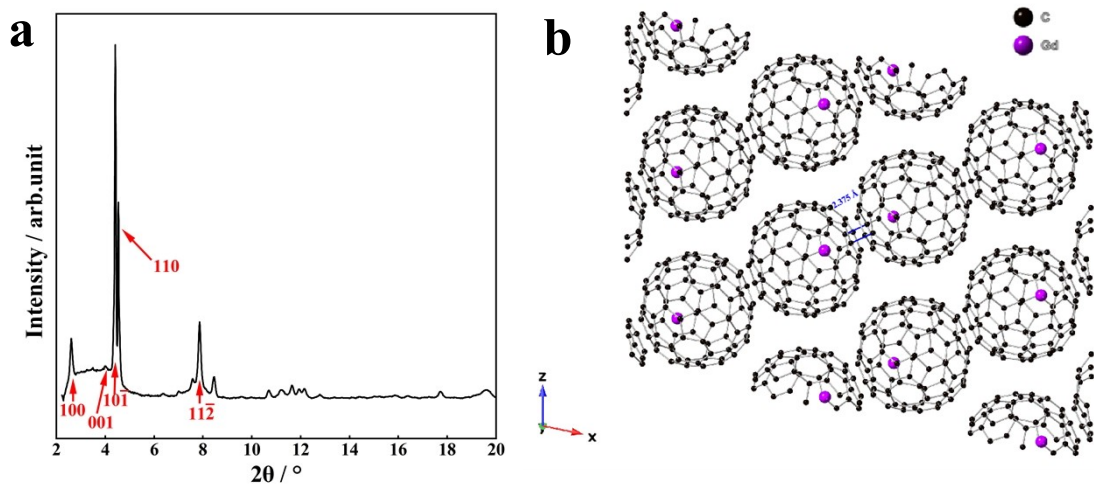


Figure. S1. (a)XRD of the polycrystalline Gd@C₈₂ raw material at ambient pressure. (b) We constructed the crystal structure of Gd@C₈₂ with a monoclinic lattice with a =15.83 Å b =11.15 Å c =10.50 Å , beta=101.83° and a *P*2₁ space group at ambient conditions, referring the literature

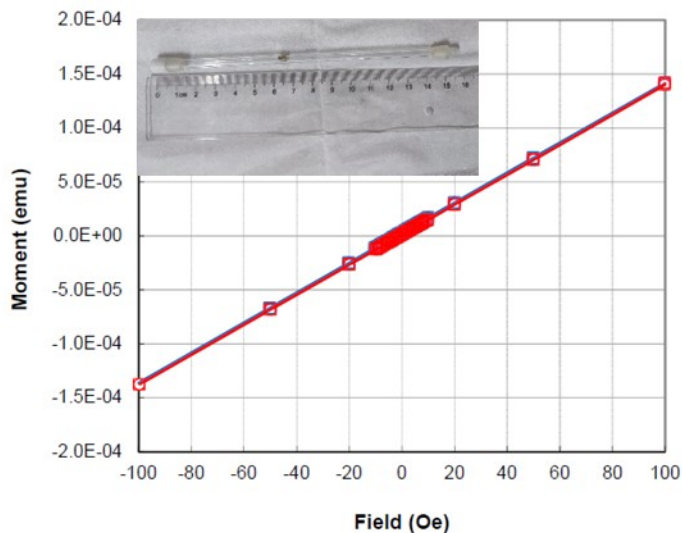


Figure. S2. The standard palladium in the sample cavity and its M-H curve. the magnetic moment calibrations for MPM3 after every cool down based on the formula: $\mu = \chi \cdot H \cdot m$, where μ is the magnetic moment of the sample, χ is the mass susceptibility of palladium at 298 K (5.25×10^{-6} emu/Oe-g), H is the magnetic field applied, and m is the mass of the palladium sample

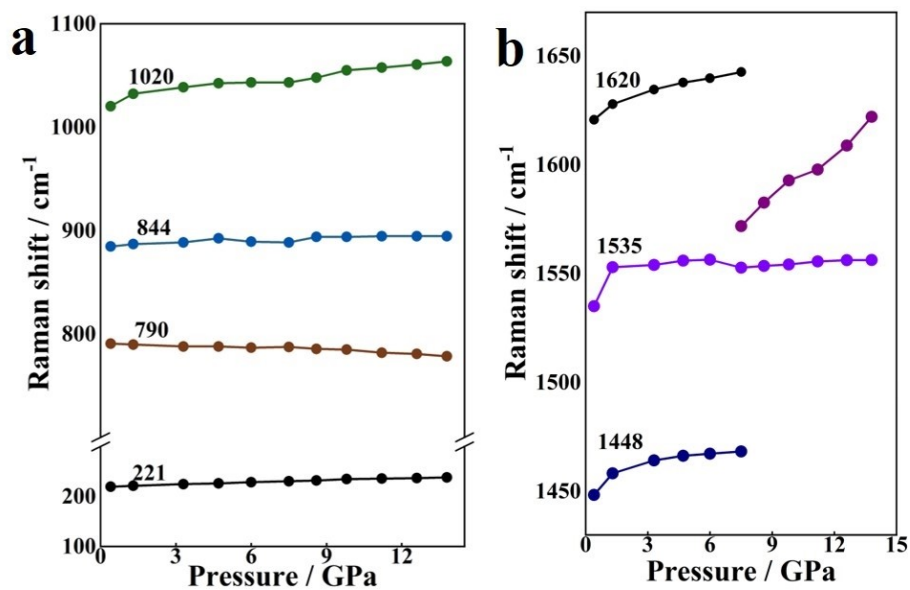


Figure. S3. peak move of Raman spectra (a) 0-1100 cm^{-1} (b) 1400-1700 cm^{-1}

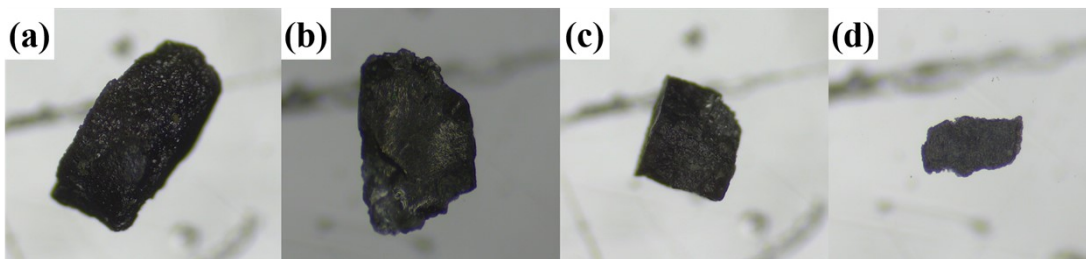


Figure. S4. The images of typical doped diamond sample (a) 15 GPa 1800 °C. (b)22 GPa 1800 °C. (c)22 GPa 2000 °C. (d)22 GPa 2100 °C.

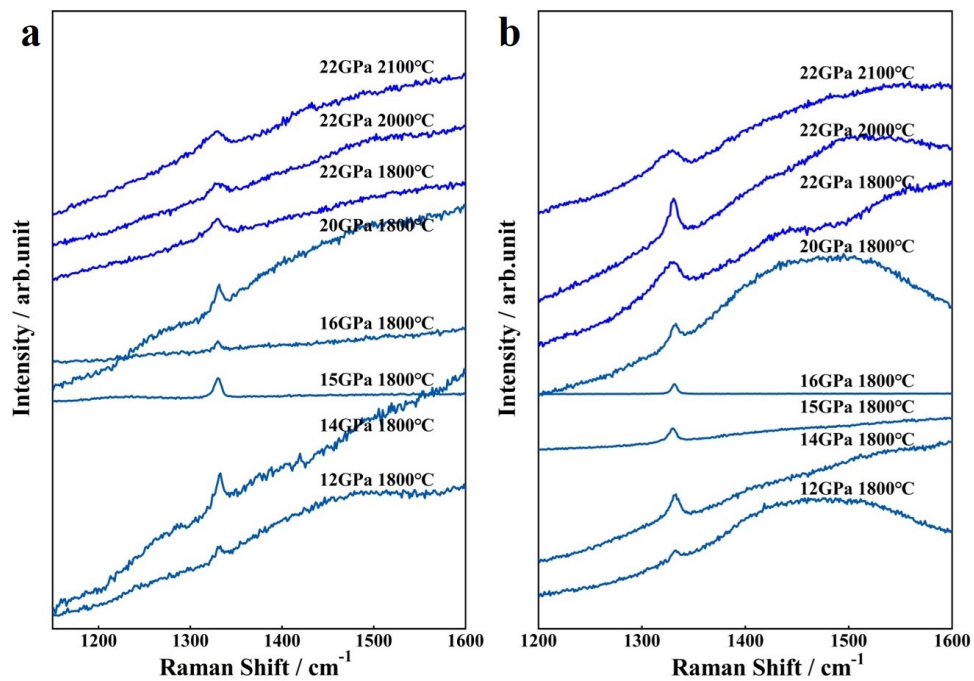


Figure. S5. Raman spectra of samples recovered from different pressure and different temperature (a) 488 nm laser and (b) 532 nm laser.

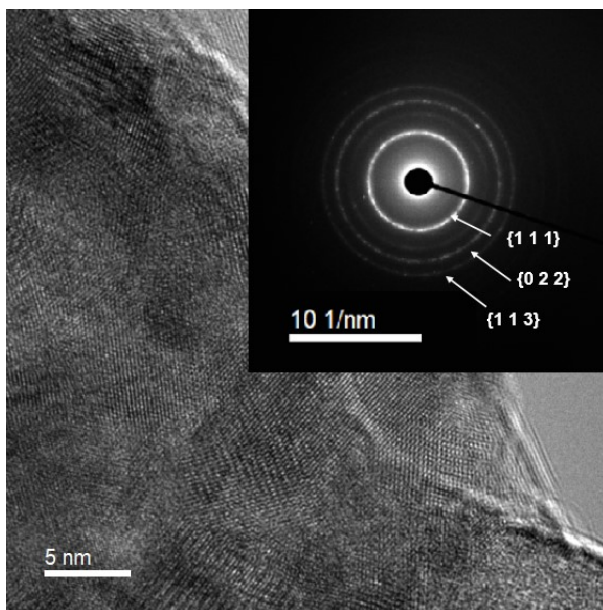


Figure. S6. HRTEM and selected area electron diffraction images of the Gd-doped diamond recovered from 15 GPa and 1800 °C.

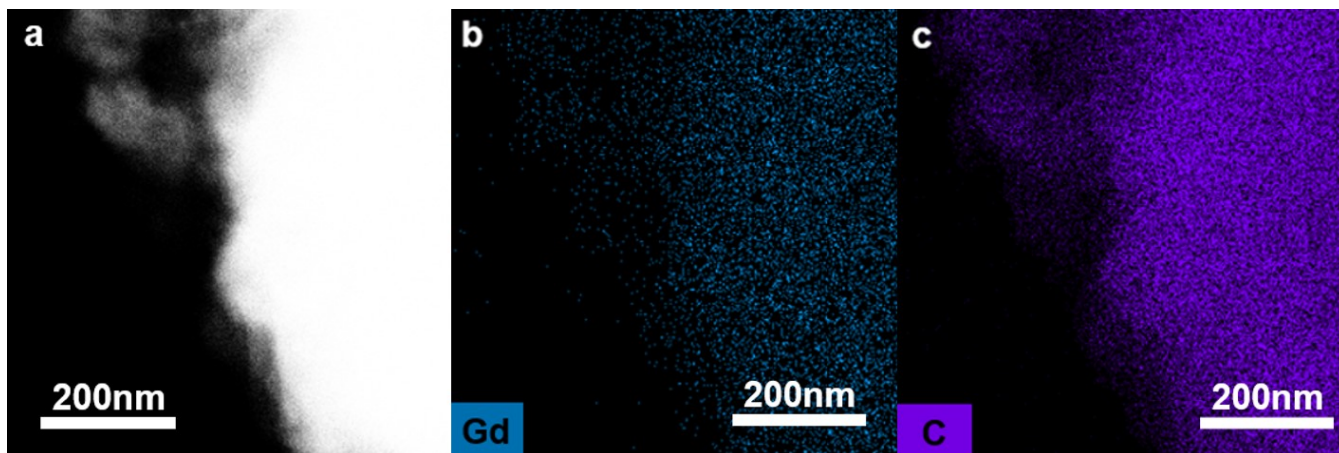


Figure. S7. (a) High angle annular dark-field scanning transmission electron microscopy STEM image of Gd@C₈₂. (b) Distribution of Gadolinium element of figure a obtained by EDS elemental mapping. (c) Distribution of carbon element of figure a.

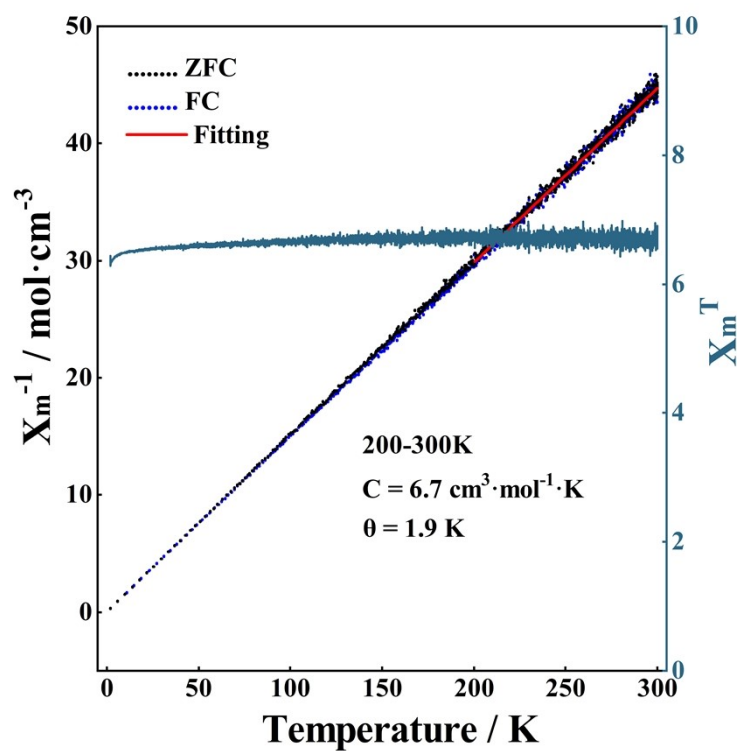


Figure. S8. M-T curve of raw material Gd@C₈₂.